NSN 5961-01-117-8261

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Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-117-8261 **Overall Length:** Between 0.225 inches and 0.255 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-18 **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 45.0 breakdown voltage, collector-to-base, emitter open and 45.0 breakdown voltage, collector-to-emitter, base open and 5.0 breakdown voltage, emitter-to-base, collector open **Power Rating Per Characteristic:** 600.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** With lens cap; internal junction configuration: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli